

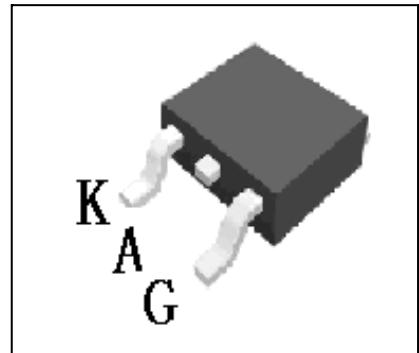


YANGZHOU POSITIONING TECH.CO.,LTD

PSTSK008DRP **SCR_S**

● Package

T0-252



● Main Feature (T_j=25°C)

Symbol	Value	Unit
I _{T(AV)}	7.5	A
V _{DRM} / V _{RRM}	≥ 1000	V
I _{GT}	1 to 15	mA

● Absolute ratings (Limiting Values)

Symbol	Parameter	Value	Unit
I _{T(RMS)}	RMS on-state current (180° conduction angle)	12	A
I _{T(AV)}	AV on-state current (180° conduction angle)	7.5	A
I _{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	100	A
I ² t	(tp=10ms)	50	A ² s
I _{GM}	Peak gate current(tp=20us)	2	A
P _{GM}	Peak gate power	5	W
P _{G(AV)}	Average gate power	0.5	W
T _{stg}	Storage temperature	-40--+150	°C
T _j	Operating junction temperature	-40--+125	°C

● Thermal Resistances

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case	1.3	K/W
R _{th} (j-a)	Junction to ambient	60	K/W



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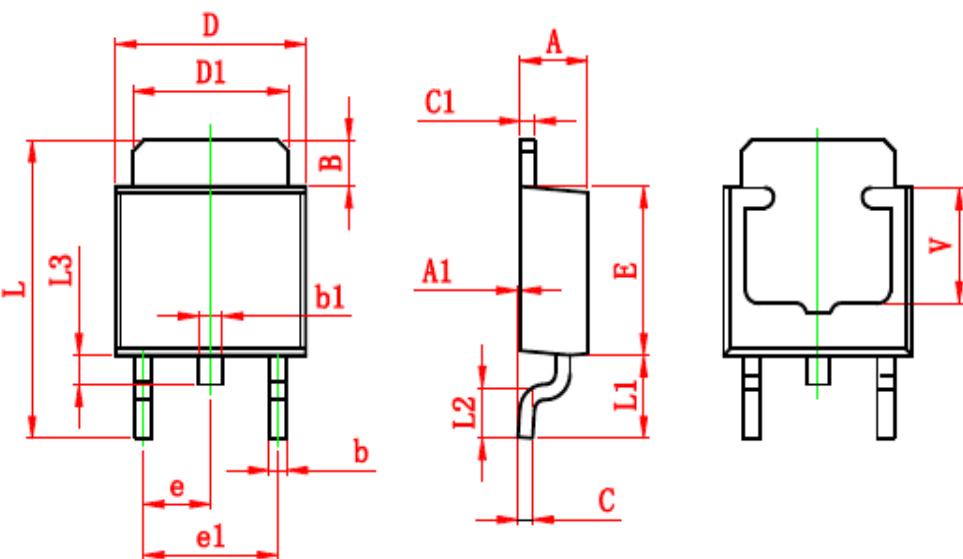
●Electrical characteristics ($T_j=25^\circ\text{C}$ unless otherwise stated)

Symbol	Test Conditions	Value			Unit
		Min	Type	Max	
I_{GT}	$V_D=6\text{V}$, $R_L=100\ \Omega$	1	5	15	mA
V_{GT}	$V_D=12\text{V}$, $R_L=100\ \Omega$	-----	0.7	0.8	V
V_{GD}	$V_D=V_{DRM}$, $R_L=3.3\text{K}\ \Omega$ $T_j=110^\circ\text{C}$	0.2	-----	-----	V
I_H	$I_T=100\text{mA}$ Gate Open	-----	9	20	mA
dV/dt	$V_D=67\% V_{DRM}$, GateOpen, $T_j=125^\circ\text{C}$	50	125	-----	v/ μ s
V_{TM}	$I_T=16\text{A}, tp=380\ \mu\text{s}$	-----	-----	1.7	V
I_{DRM}	$V_D=V_{DRM}$	$T_j=25^\circ\text{C}$	-----	20	uA
I_{RRM}	$V_R=V_{RRM}$	$T_j=110^\circ\text{C}$	-----	300	uA



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●Measure of package
(TO-252 Type)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

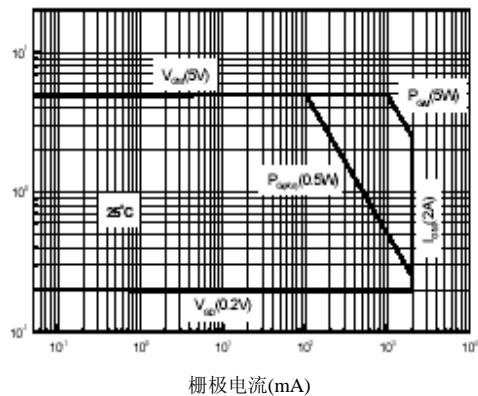
Unit: mm



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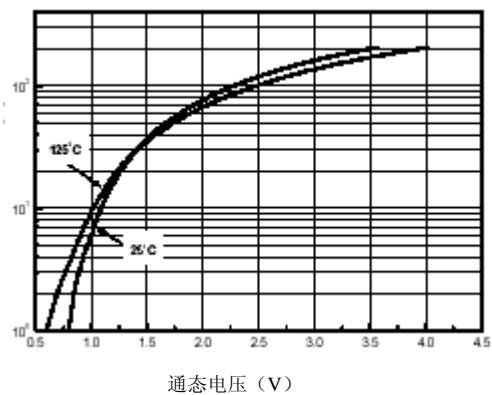
图一、栅极特性

栅极电压(v)

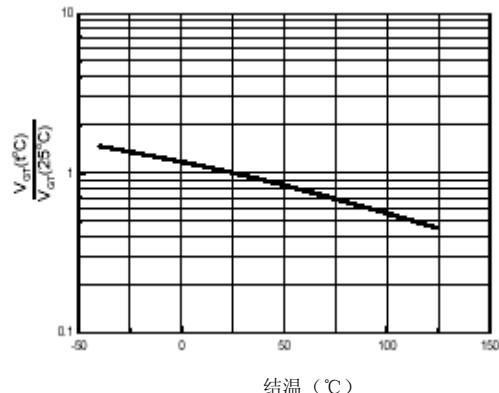


图三、典型正向压降

通态电流 (A)

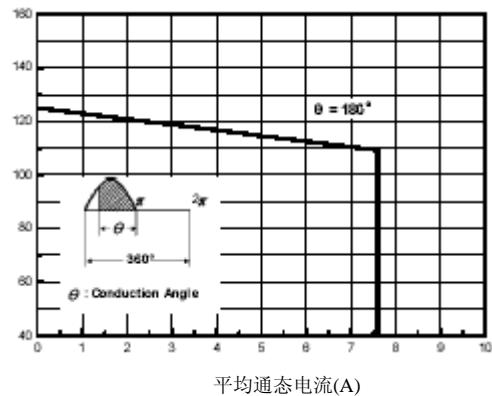


图五、典型栅极触发电压----结温



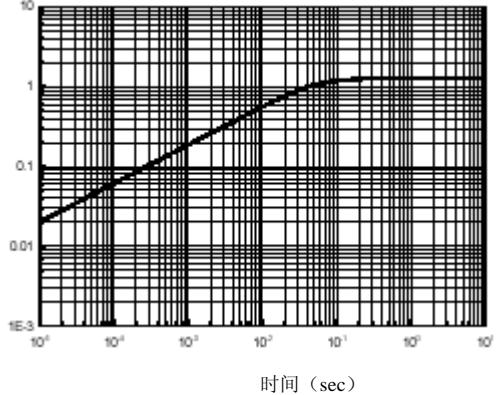
图二、最大外壳温度

最大允许外壳温度 ($^\circ\text{C}$)

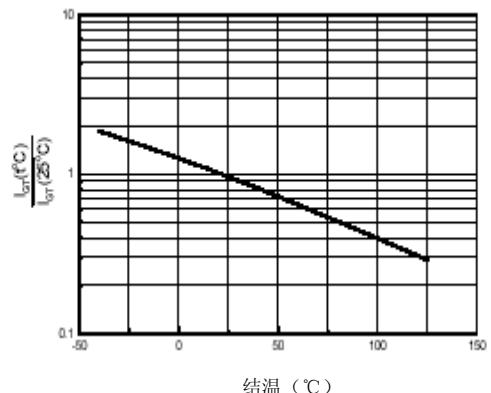


图四、热响应

瞬态热阻 ($^\circ\text{C}/\text{W}$)



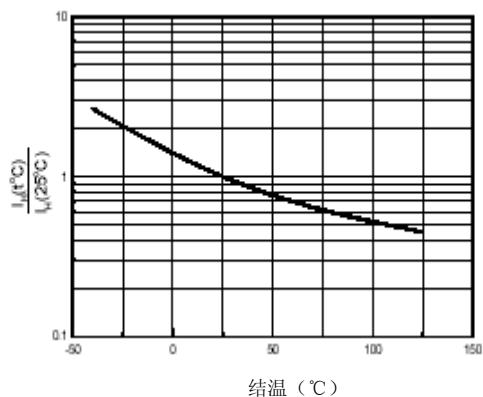
图六、典型栅极触发电流----结温





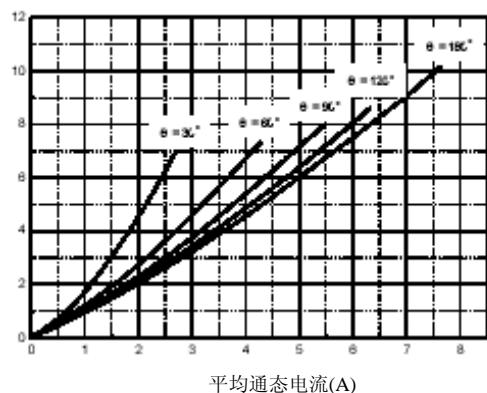
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图七、典型维持电流图



八、功耗

最大平均功耗 (W)



●Electrocircuit:

